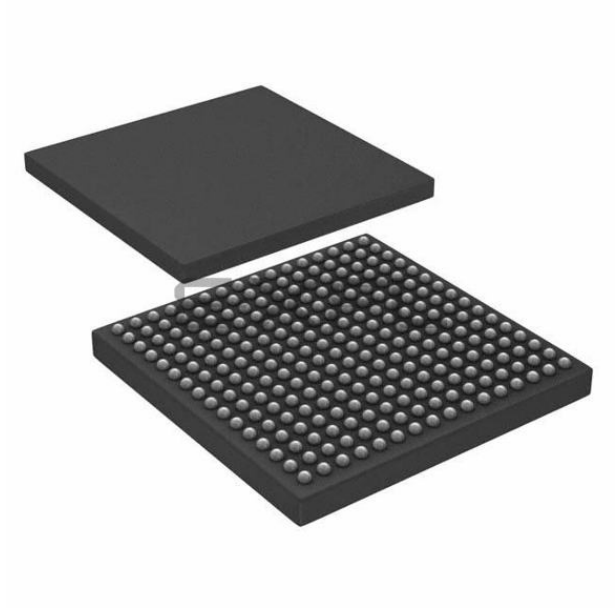

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

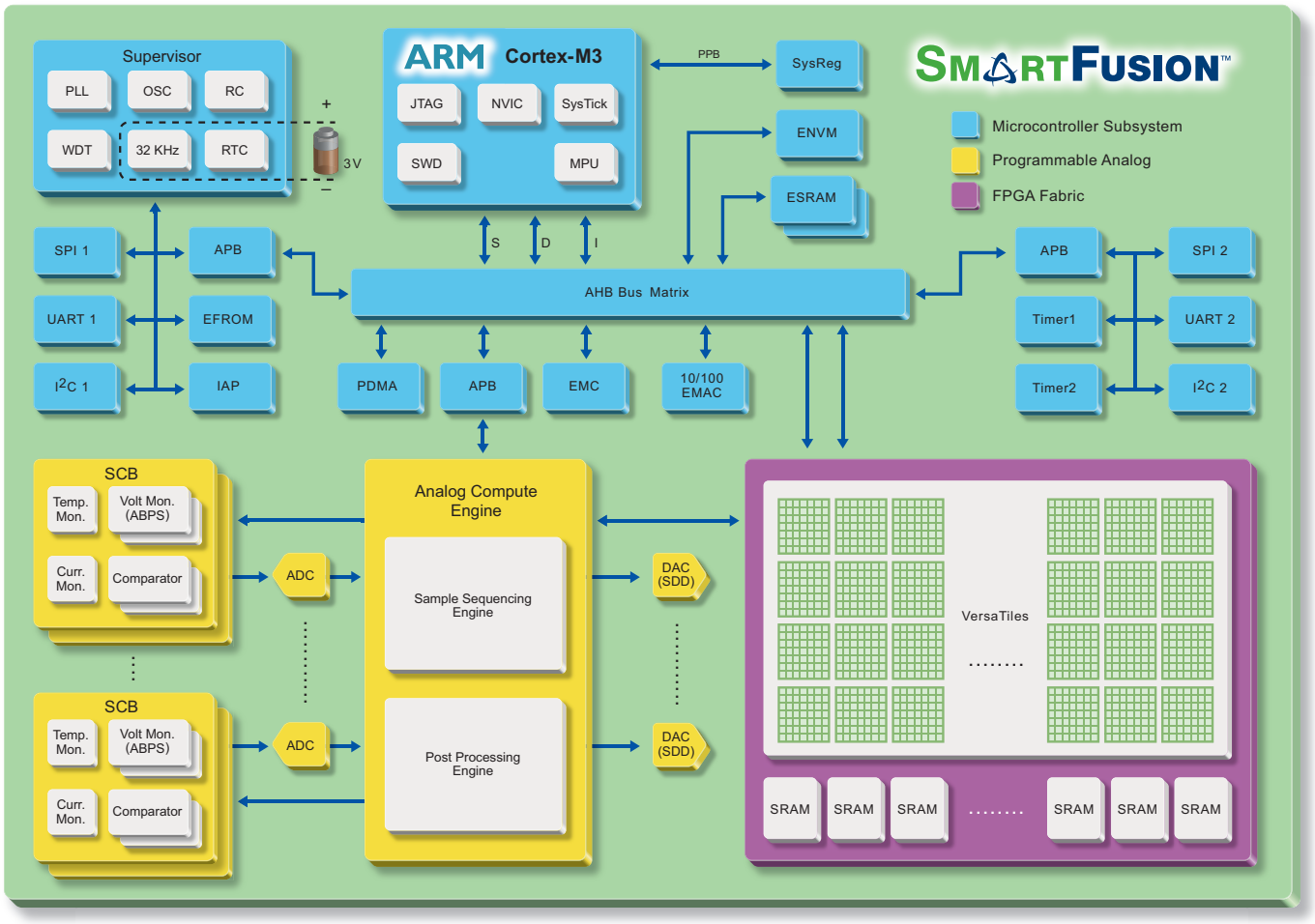
Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	100MHz
Primary Attributes	ProASIC®3 FPGA, 500K Gates, 11520 D-Flip-Flops
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f500m3g-1fg256

SmartFusion cSoC Block Diagram



Legend:

SDD – Sigma-delta DAC
SCB – Signal conditioning block
PDMA – Peripheral DMA
IAP – In-application programming
ABPS – Active bipolar prescaler
WDT – Watchdog Timer
SWD – Serial Wire Debug

Table 2-14 • Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F500	
PAC24	Current Monitor Power Contribution	See Table 2-93 on page 2-78	–	1.03			mW
PAC25	ABPS Power Contribution	See Table 2-96 on page 2-82	–	0.70			mW
PAC26	Sigma-Delta DAC Power Contribution[2]	See Table 2-98 on page 2-85	–	0.58			mW
PAC27	Comparator Power Contribution	See Table 2-97 on page 2-84	–	1.02			mW
PAC28	Voltage Regulator Power Contribution[3]	See Table 2-99 on page 2-87	–	36.30			mW

Notes:

1. *For a different use of MSS peripherals and resources, refer to SmartPower.*
2. *Assumes Input = Half Scale Operation mode.*
3. *Assumes 100 mA load on 1.5 V domain.*

Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs

Parameter	Definition	Power Supply		Device			Units
		Name	Domain	A2F060	A2F200	A2F200	
PDC1	Core static power contribution in SoC mode	VCC	1.5 V	11.10	23.70	37.95	mW
PDC2	Device static power contribution in Standby Mode	See Table 2-8 on page 2-10	–	11.10	23.70	37.95	mW
PDC3	Device static power contribution in Time Keeping mode	See Table 2-8 on page 2-10	3.3 V	33.00	33.00	33.00	µW
PDC7	Static contribution per input pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-10 and Table 2-11 on page 2-11.				
PDC8	Static contribution per output pin (standard dependent contribution)	VCCxxxxIOBx/VCC	See Table 2-12 and Table 2-13 on page 2-11.				
PDC9	Static contribution per PLL	VCC	1.5 V	2.55	2.55	2.55	mW

Table 2-16 • eNVM Dynamic Power Consumption

Parameter	Description	Condition	Min.	Typ.	Max.	Units
eNVM System	eNVM array operating power	Idle		795		µA
		Read operation	See Table 2-14 on page 2-12.			
		Erase		900		µA
		Write		900		µA
PNVMCTRL	eNVM controller operating power			20		µW/MHz

Table 2-21 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial Conditions in all I/O Bank Types

	Commercial	
	I_{IL}	I_{IH}
DC I/O Standards	**µA**	**µA**
3.3 V LVTTL / 3.3 V LVCMOS	15	15
2.5 V LVCMOS	15	15
1.8 V LVCMOS	15	15
1.5 V LVCMOS	15	15
3.3 V PCI	15	15
3.3 V PCI-X	15	15

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-22 • Summary of AC Measuring Points Applicable to All I/O Bank Types

Standard	Measuring Trip Point (V_{trip})
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
3.3 V PCI	0.285 * VCCxxxxIOBx (RR)
	0.615 * VCCxxxxIOBx (FF)
3.3 V PCI-X	0.285 * VCCxxxxIOBx (RR)
	0.615 * VCCxxxxIOBx (FF)
LVDS	Cross point
LVPECL	Cross point

Table 2-23 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to pad delay through the output buffer
t_{PY}	Pad to data delay through the input buffer
t_{DOUT}	Data to output buffer delay through the I/O interface
t_{EOUT}	Enable to output buffer tristate control delay through the I/O interface
t_{DIN}	Input buffer to data delay through the I/O interface
t_{HZ}	Enable to pad delay through the output buffer—High to Z
t_{ZH}	Enable to pad delay through the output buffer—Z to High
t_{LZ}	Enable to pad delay through the output buffer—Low to Z
t_{ZL}	Enable to pad delay through the output buffer—Z to Low
t_{ZHS}	Enable to pad delay through the output buffer with delayed enable—Z to High
t_{ZLS}	Enable to pad delay through the output buffer with delayed enable—Z to Low

Table 2-28 • I/O Output Buffer Maximum Resistances[1]
Applicable to MSS I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	8mA	50	150
2.5 V LVCMOS	8 mA	50	100
1.8 V LVCMOS	4 mA	100	112
1.5 V LVCMOS	2 mA	200	224

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (V_{CCImax} – V_{OHspec}) / I_{OHspec}$

Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

VCCxxxxIOBx	$R_{(WEAK\ PULL\text{-}UP)}$[1] ($\Omega$)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] ($\Omega$)	
	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)} = (VCCImax – VOHspec) / I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{(WEAK\ PULL\text{-}DOWN\text{-}MIN)}$

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than 2200 operation hours to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

***Table 2-32* • Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

***Table 2-33* • Schmitt Trigger Input Hysteresis**
Hysteresis Voltage Value (typical) for Schmitt Mode Input Buffers

Input Buffer Configuration	Hysteresis Value (typical)
3.3 V LVTTL / LVCMOS / PCI / PCI-X (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV

***Table 2-34* • I/O Input Rise Time, Fall Time, and Related I/O Reliability**

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS	No requirement	10 ns *	20 years (100°C)
LVDS/B-LVDS/ M-LVDS/LVPECL	No requirement	10 ns *	10 years (100°C)

*Note: *The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi SoC Products Group recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.*

Timing Characteristics

Table 2-50 • 1.8 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	11.06	0.04	1.14	0.39	8.61	11.06	2.61	1.59	10.67	13.12	ns
	–1	0.50	9.22	0.03	0.95	0.32	7.17	9.22	2.18	1.33	8.89	10.93	ns
4 mA	Std.	0.60	6.46	0.04	1.14	0.39	5.53	6.46	3.04	2.66	7.59	8.51	ns
	–1	0.50	5.38	0.03	0.95	0.32	4.61	5.38	2.54	2.22	6.33	7.10	ns
6 mA	Std.	0.60	4.16	0.04	1.14	0.39	3.99	4.16	3.34	3.18	6.05	6.22	ns
	–1	0.50	3.47	0.03	0.95	0.32	3.32	3.47	2.78	2.65	5.04	5.18	ns
8 mA	Std.	0.60	3.69	0.04	1.14	0.39	3.76	3.67	3.40	3.31	5.81	5.73	ns
	–1	0.50	3.07	0.03	0.95	0.32	3.13	3.06	2.84	2.76	4.85	4.78	ns
12 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns
16 mA	Std.	0.60	3.38	0.04	1.14	0.39	3.44	2.86	3.50	3.82	5.50	4.91	ns
	–1	0.50	2.81	0.03	0.95	0.32	2.87	2.38	2.92	3.18	4.58	4.10	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-51 • 1.8 V LVCMOS Low Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.60	14.24	0.04	1.14	0.39	13.47	14.24	2.62	1.54	15.53	16.30	ns
	–1	0.50	11.87	0.03	0.95	0.32	11.23	11.87	2.18	1.28	12.94	13.59	ns
4 mA	Std.	0.60	9.74	0.04	1.14	0.39	9.92	9.62	3.05	2.57	11.98	11.68	ns
	–1	0.50	8.11	0.03	0.95	0.32	8.26	8.02	2.54	2.14	9.98	9.74	ns
6 mA	Std.	0.60	7.67	0.04	1.14	0.39	7.81	7.24	3.34	3.08	9.87	9.30	ns
	–1	0.50	6.39	0.03	0.95	0.32	6.51	6.03	2.79	2.56	8.23	7.75	ns
8 mA	Std.	0.60	7.15	0.04	1.14	0.39	7.29	6.75	3.41	3.21	9.34	8.80	ns
	–1	0.50	5.96	0.03	0.95	0.32	6.07	5.62	2.84	2.68	7.79	7.34	ns
12 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns
16 mA	Std.	0.60	6.76	0.04	1.14	0.39	6.89	6.75	3.50	3.70	8.95	8.81	ns
	–1	0.50	5.64	0.03	0.95	0.32	5.74	5.62	2.92	3.08	7.46	7.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-52 • 1.8 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 1.7 V
Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	Std.	0.22	2.77	0.09	1.09	1.64	0.22	2.82	2.72	2.21	2.25	ns
	–1	0.18	2.31	0.07	0.91	1.37	0.18	2.35	2.27	1.84	1.87	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

***Table 2-70* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

* *See Figure 2-15 on page 2-46 for more information.*

Input Register

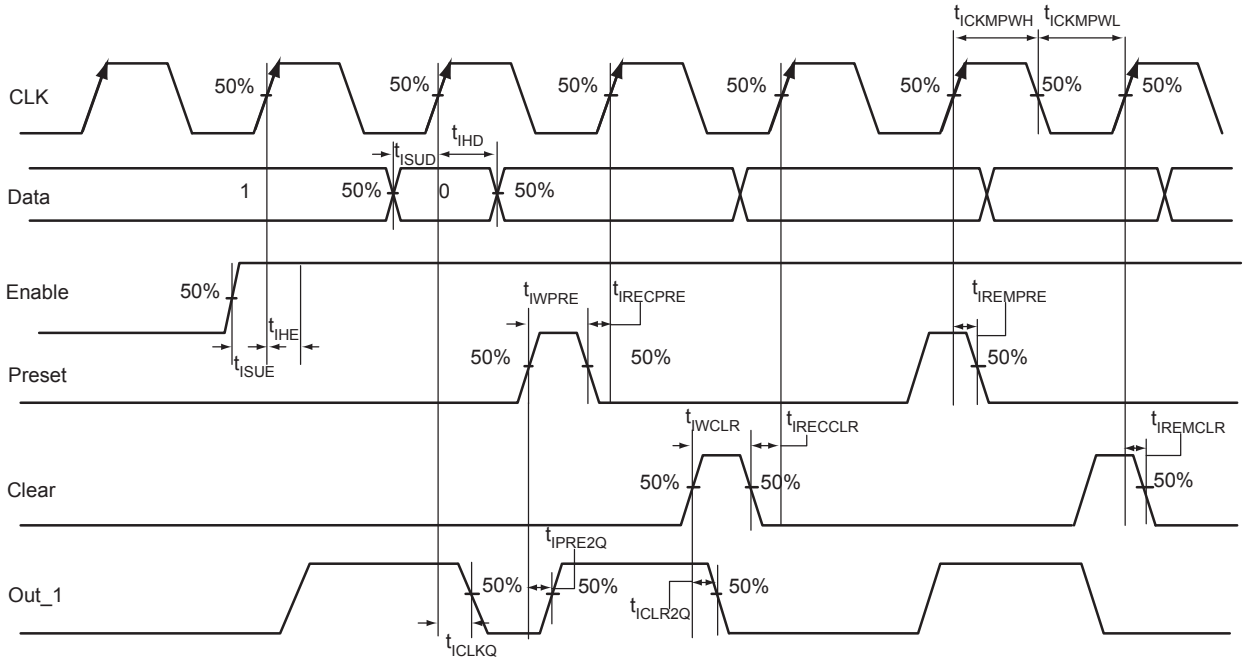


Figure 2-16 • **Input Register Timing Diagram**

Timing Characteristics

Table 2-71 • **Input Data Register Propagation Delays**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.29	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.27	0.32	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.38	0.45	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.46	0.55	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.46	0.55	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.23	0.27	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.23	0.27	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.22	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.22	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.36	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.32	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

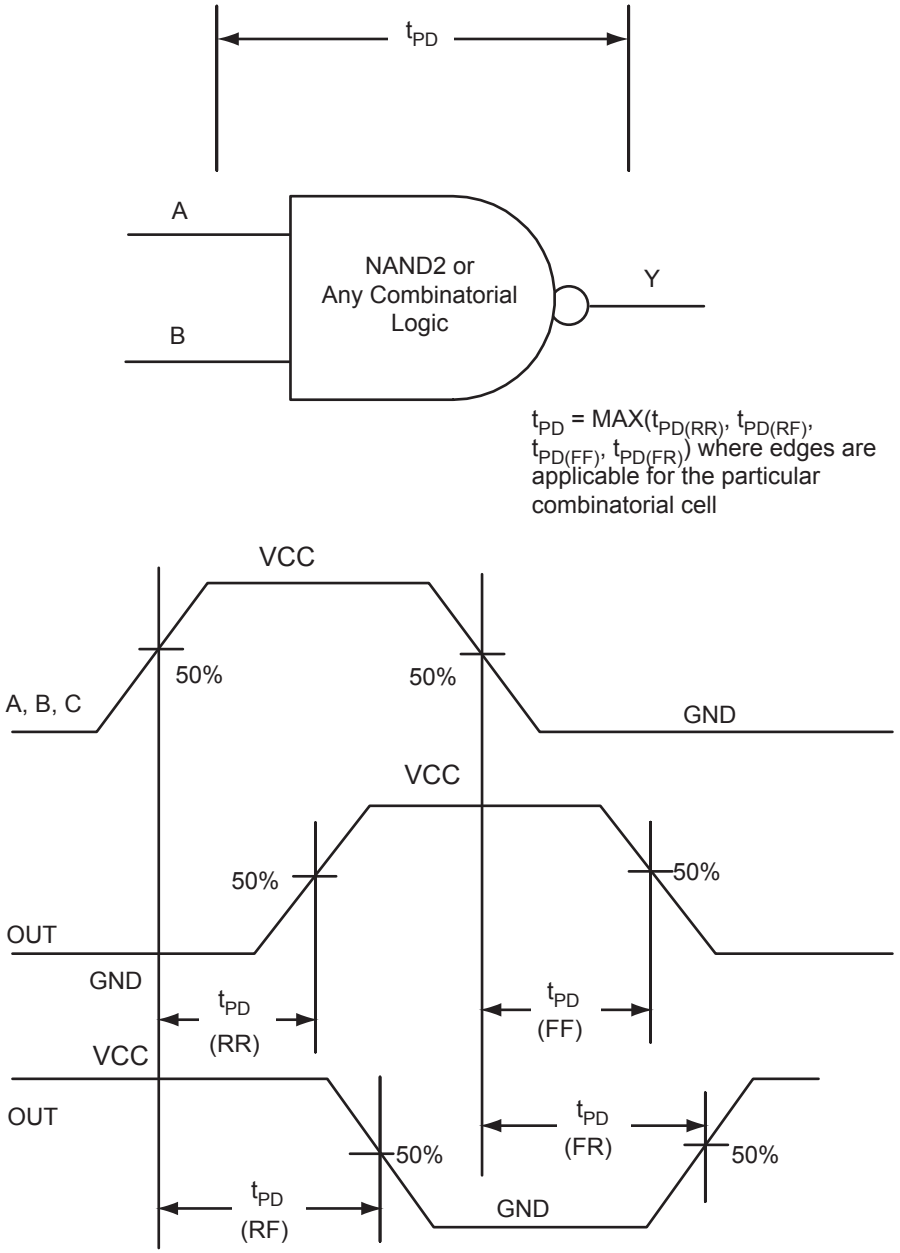


Figure 2-24 • **Timing Model and Waveforms**

Embedded Design

Microsemi offers FREE SoftConsole Eclipse based IDE, which includes the GNU C/C++ compiler and GDB debugger. Microsemi also offers evaluation versions of software from Keil and IAR, with full versions available from respective suppliers.

Analog Design

The MSS configurator provides graphical configuration for current, voltage and temperature monitors, sample sequencing setup and post-processing configuration, as well as DAC output.

The MSS configurator creates a bridge between the FPGA fabric and embedded designers so device configuration can be easily shared between multiple developers.

The MSS configurator includes the following:

- A simple configurator for the embedded designer to control the MSS peripherals and I/Os
- A method to import and view a hardware configuration from the FPGA flow into the embedded flow containing the memory map
- Automatic generation of drivers for any peripherals or soft IP used in the system configuration
- Comprehensive analog configuration for the programmable analog components
- Creation of a standard MSS block to be used in SmartDesign for connection of FPGA fabric designs and IP

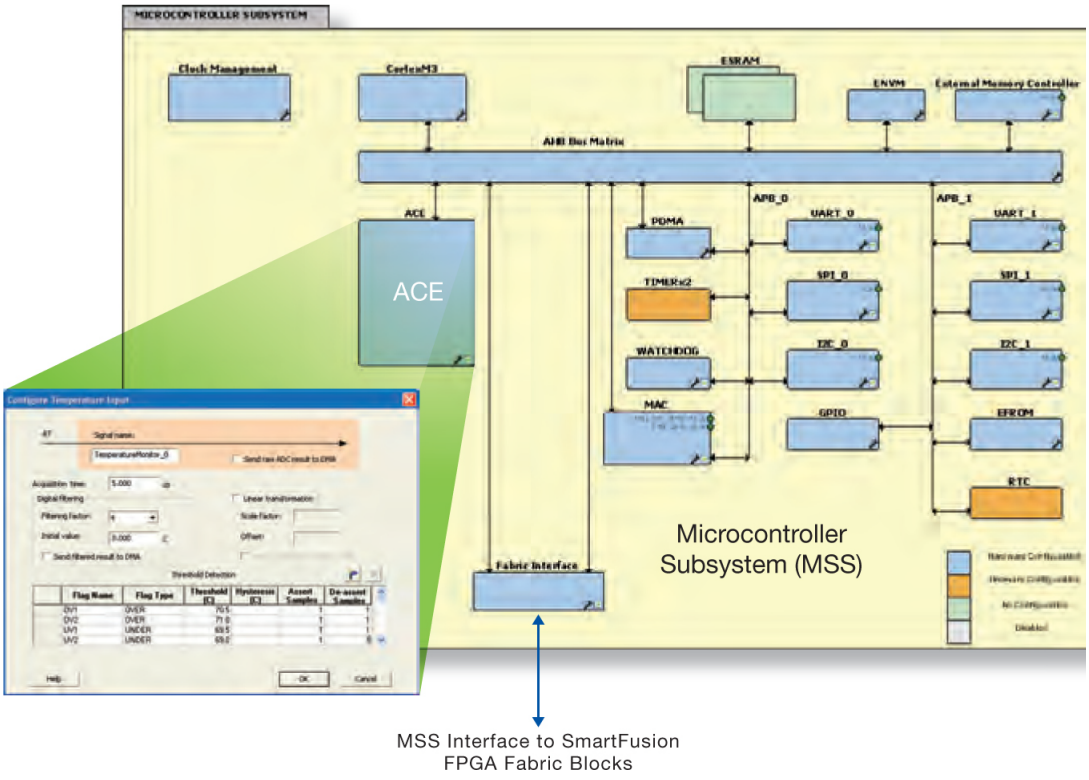


Figure 3-2 • **MSS Configurator**

Special Function Pins

Name	Type	Polarity/Bus Size	Description
NC			No connect This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.
DC			Do not connect. This pin should not be connected to any signals on the PCB. These pins should be left unconnected.
LPXIN	In	1	Low power 32 KHz crystal oscillator. Input from the 32 KHz oscillator. Pin for connecting a low power 32 KHz watch crystal. If not used, the LPXIN pin can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the *SmartFusion Microcontroller Subsystem User's Guide*.
LPXOUT	In	1	Low power 32 KHz crystal oscillator. Output to the 32 KHz oscillator. Pin for connecting a low power 32 KHz watch crystal. If not used, the LPXOUT pin can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the *SmartFusion Microcontroller Subsystem User's Guide*.
MAINXIN	In	1	Main crystal oscillator circuit. Input to the crystal oscillator circuit. Pin for connecting an external crystal, ceramic resonator, or RC network. When using an external crystal or ceramic oscillator, external capacitors are also recommended. Refer to documentation from the crystal oscillator manufacturer for proper capacitor value. If an external RC network or clock input is used, the RC components are connected to the MAINXIN pin, with MAINXOUT left floating. When the main crystal oscillator is not being used, MAINXIN and MAINXOUT pins can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the *SmartFusion Microcontroller Subsystem User's Guide*.
MAINXOUT	Out	1	Main crystal oscillator circuit. Output from the crystal oscillator circuit. Pin for connecting external crystal or ceramic resonator. When using an external crystal or ceramic oscillator, external capacitors are also recommended. Refer to documentation from the crystal oscillator manufacturer for proper capacitor value. If an external RC network or clock input is used, the RC components are connected to the MAINXIN pin, with MAINXOUT left floating. When the main crystal oscillator is not being used, MAINXIN and MAINXOUT pins can be left floating. For more information, see the PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators section in the *SmartFusion Microcontroller Subsystem User's Guide*.

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
A1	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A2	GNDQ	GNDQ	GNDQ
A3	EMC_CLK/IO00NDB0V0	EMC_CLK/GAA0/IO00NDB0V0	EMC_CLK/GAA0/IO02NDB0V0
A4	EMC_RW_N/IO00PDB0V0	EMC_RW_N/GAA1/IO00PDB0V0	EMC_RW_N/GAA1/IO02PDB0V0
A5	GND	GND	GND
A6	EMC_CS1_N/IO01PDB0V0	EMC_CS1_N/GAB1/IO01PDB0V0	EMC_CS1_N/GAB1/IO05PDB0V0
A7	EMC_CS0_N/IO01NDB0V0	EMC_CS0_N/GAB0/IO01NDB0V0	EMC_CS0_N/GAB0/IO05NDB0V0
A8	EMC_AB[0]/IO04NPB0V0	EMC_AB[0]/IO04NPB0V0	EMC_AB[0]/IO06NPB0V0
A9	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A10	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO10NDB0V0
A11	EMC_AB[8]/IO08NPB0V0	EMC_AB[8]/IO08NPB0V0	EMC_AB[8]/IO13NPB0V0
A12	EMC_AB[14]/IO11NPB0V0	EMC_AB[14]/IO11NPB0V0	EMC_AB[14]/IO15NPB0V0
A13	GND	GND	GND
A14	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO18NDB0V0
A15	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO20NDB0V0
A16	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO20PDB0V0
A17	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A18	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO21NDB0V0
A19	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO21PDB0V0
A20	GNDQ	GNDQ	GNDQ
A21	GND	GND	GND
AA1	ADC1	ABPS1	ABPS1
AA2	GNDAQ	GNDAQ	GNDAQ
AA3	GNDA	GNDA	GNDA
AA4	VCC33N	VCC33N	VCC33N
AA5	SDD0	SDD0	SDD0
AA6	ADC0	ABPS0	ABPS0
AA7	NC	GNDTM0	GNDTM0
AA8	NC	ABPS2	ABPS2
AA9	NC	VAREF0	VAREF0
AA10	NC	GND15ADC0	GND15ADC0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
A1	GND	GND	GND
A2	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A3	EMC_AB[0]/IO04NDB0V0	EMC_AB[0]/IO04NDB0V0	EMC_AB[0]/IO06NDB0V0
A4	EMC_AB[1]/IO04PDB0V0	EMC_AB[1]/IO04PDB0V0	EMC_AB[1]/IO06PDB0V0
A5	GND	GND	GND
A6	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO09PDB0V0
A7	EMC_AB[5]/IO06PDB0V0	EMC_AB[5]/IO06PDB0V0	EMC_AB[5]/IO10PDB0V0
A8	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A9	GND	GND	GND
A10	EMC_AB[14]/IO11NDB0V0	EMC_AB[14]/IO11NDB0V0	EMC_AB[14]/IO15NDB0V0
A11	EMC_AB[15]/IO11PDB0V0	EMC_AB[15]/IO11PDB0V0	EMC_AB[15]/IO15PDB0V0
A12	GND	GND	GND
A13	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO21NDB0V0
A14	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO20NDB0V0
A15	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
A16	GND	GND	GND
B1	EMC_DB[15]/IO45PDB5V0	EMC_DB[15]/GAA2/IO71PDB5V0	EMC_DB[15]/GAA2/IO88PDB5V0
B2	GND	GND	GND
B3	EMC_BYTEN[1]/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO07PDB0V0
B4	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO08NDB0V0
B5	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO08PDB0V0
B6	EMC_AB[2]/IO05NDB0V0	EMC_AB[2]/IO05NDB0V0	EMC_AB[2]/IO09NDB0V0
B7	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO10NDB0V0
B8	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO13PDB0V0
B9	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO14NDB0V0
B10	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO14PDB0V0
B11	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO17NDB0V0
B12	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO18NDB0V0
B13	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO21PDB0V0
B14	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO20PDB0V0
B15	GND	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
F14	IO21NDB1V0	GCB0/IO27NDB1V0	GCB0/IO34NDB1V0
F15	GND	GND	GND
F16	VCCENVM	VCCENVM	VCCENVM
G1	EMC_DB[8]/IO40NDB5V0	EMC_DB[8]/GEC0/IO63NDB5V0	EMC_DB[8]/GEC0/IO80NDB5V0
G2	EMC_DB[7]/IO39PDB5V0	EMC_DB[7]/GEB1/IO62PDB5V0	EMC_DB[7]/GEB1/IO79PDB5V0
G3	EMC_DB[6]/IO39NDB5V0	EMC_DB[6]/GEB0/IO62NDB5V0	EMC_DB[6]/GEB0/IO79NDB5V0
G4	GFC2/IO41PDB5V0	GFC2/IO67PDB5V0	GFC2/IO84PDB5V0
G5	IO41NDB5V0	IO67NDB5V0	IO84NDB5V0
G6	GND	GND	GND
G7	VCC	VCC	VCC
G8	GND	GND	GND
G9	VCC	VCC	VCC
G10	GND	GND	GND
G11	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
G12	VPP	VPP	VPP
G13	TRSTB	TRSTB	TRSTB
G14	TMS	TMS	TMS
G15	TCK	TCK	TCK
G16	GNDENVM	GNDENVM	GNDENVM
H1	GND	GND	GND
H2	EMC_DB[5]/IO38PPB5V0	EMC_DB[5]/GEA1/IO61PPB5V0	EMC_DB[5]/GEA1/IO78PPB5V0
H3	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
H4	EMC_DB[1]/IO36PDB5V0	EMC_DB[1]/GEB2/IO59PDB5V0	EMC_DB[1]/GEB2/IO76PDB5V0
H5	EMC_DB[0]/IO36NDB5V0	EMC_DB[0]/GEA2/IO59NDB5V0	EMC_DB[0]/GEA2/IO76NDB5V0
H6	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
H7	GND	GND	GND
H8	VCC	VCC	VCC
H9	GND	GND	GND
H10	VCC	VCC	VCC
H11	GND	GND	GND
H12	VJTAG	VJTAG	VJTAG

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
C15	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO17PDB0V0
C16	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO20NDB0V0
C17	EMC_AB[22]/IO15NDB0V0	EMC_AB[22]/IO19NDB0V0
C18	EMC_AB[23]/IO15PDB0V0	EMC_AB[23]/IO19PDB0V0
C19	GBA0/IO19NPB0V0	GBA0/IO23NPB0V0
C20	NC	NC
C21	GBC2/IO21PDB1V0	GBC2/IO30PDB1V0
C22	GBB2/IO20NDB1V0	GBB2/IO27NDB1V0
D1	GND	GND
D2	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
D3	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
D4	NC	NC
D5	NC	NC
D6	GND	GND
D7	NC	IO00NPB0V0
D8	NC	IO03NPB0V0
D9	GND	GND
D10	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO08NDB0V0
D11	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO11NDB0V0
D12	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO11PDB0V0
D13	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO13PDB0V0
D14	GND	GND
D15	GBC1/IO17PPB0V0	GBC1/IO22PPB0V0
D16	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO20PDB0V0
D17	GND	GND
D18	GBA1/IO19PPB0V0	GBA1/IO23PPB0V0
D19	NC	NC
D20	NC	NC
D21	IO21NDB1V0	IO30NDB1V0
D22	GND	GND
E1	GFC2/IO67PPB5V0	GFC2/IO84PPB5V0
E2	VCCFPGAIOB5	VCCFPGAIOB5
E3	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
E4	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
F17	NC	IO25PPB1V0
F18	VCCFPGAIOB1	VCCFPGAIOB1
F19	IO23NDB1V0	IO28NDB1V0
F20	NC	IO31PDB1V0
F21	NC	IO31NDB1V0
F22	IO22PDB1V0	IO32PDB1V0
G1	GND	GND
G2	GFB0/IO65NPB5V0	GFB0/IO82NPB5V0
G3	EMC_DB[9]/GEC1/IO63PDB5V0	EMC_DB[9]/GEC1/IO80PDB5V0
G4	GFC1/IO66PPB5V0	GFC1/IO83PPB5V0
G5	EMC_DB[11]/IO69PPB5V0	EMC_DB[11]/IO86PPB5V0
G6	GNDQ	GNDQ
G7	NC	NC
G8	GND	GND
G9	VCCFPGAIOB0	VCCFPGAIOB0
G10	GND	GND
G11	VCCFPGAIOB0	VCCFPGAIOB0
G12	GND	GND
G13	VCCFPGAIOB0	VCCFPGAIOB0
G14	GND	GND
G15	VCCFPGAIOB0	VCCFPGAIOB0
G16	GNDQ	GNDQ
G17	NC	IO26PDB1V0
G18	NC	IO26NDB1V0
G19	GCA2/IO23PDB1V0	GCA2/IO28PDB1V0 *
G20	IO24NDB1V0	IO33NDB1V0
G21	GCB2/IO24PDB1V0	GCB2/IO33PDB1V0
G22	GND	GND
H1	EMC_DB[7]/GEB1/IO62PDB5V0	EMC_DB[7]/GEB1/IO79PDB5V0
H2	VCCFPGAIOB5	VCCFPGAIOB5
H3	EMC_DB[8]/GEC0/IO63NDB5V0	EMC_DB[8]/GEC0/IO80NDB5V0
H4	GND	GND
H5	GFC0/IO66NPB5V0	GFC0/IO83NPB5V0
H6	GFA1/IO64PDB5V0	GFA1/IO81PDB5V0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Revision	Changes	Page
Revision 3 (continued)	In Table 2-3 • Recommended Operating Conditions[5,6], the VDDBAT recommended operating range was changed from "2.97 to 3.63" to "2.7 to 3.63" (SAR 25246). Recommended operating range was changed to "3.15 to 3.45" for the following voltages: VCC33A VCC33ADCx VCC33AP VCC33SDDx VCCMAINXTAL VCCLPXTAL Two notes were added to the table (SAR 27109): 1. *The following 3.3 V supplies should be connected together while following proper noise filtering practices: VCC33A, VCC33ADCx, VCC33AP, VCC33SDDx, VCCMAINXTAL, and VCCLPXTAL.* 2. *The following 1.5 V supplies should be connected together while following proper noise filtering practices: VCC, VCC15A, and VCC15ADCx.*	2-3
	In Table 2-3 • Recommended Operating Conditions[5,6], the description for VCCLPXTAL was corrected to change "32 Hz" to "32 KHz" (SAR 27110).	2-3
	The "Power Supply Sequencing Requirement" section is new (SAR 27178).	2-4
	Table 2-8 • Power Supplies Configuration was revised to change most on/off entries to voltages. Note 5 was added, stating that "on" means proper voltage is applied. The values of 6 µA and 16 µA were removed for IDC1 and IDC2 for 3.3 V. A note was added for IDC1 and IDC2: "Power mode and Sleep mode are consuming higher current than expected in the current version of silicon. These specifications will be updated when new version of the silicon is available" (SAR 27926).	2-10
	The "Power-Down and Sleep Mode Implementation" section is new (SAR 27178).	2-11
	A note was added to Table 2-86 • SmartFusion CCC/PLL Specification, pertaining to f_{out_CCC}, stating that "one of the CCC outputs (GLA0) is used as an MSS clock and is limited to 100 MHz (maximum) by software" (SAR 26388).	2-63
	Table 2-90 • eNVM Block Timing, Worst Commercial Case Conditions: T_J = 85°C, VCC = 1.425 V was revised. Values were included for A2F200 and A2F500, for –1 and Std. speed grades. A note was added to define 6:1:1:1 and 5:1:1:1 (SAR 26166).	2-76
	The units were corrected (mV instead of V) for input referred offset voltage, GDEC[1:0] = 00 in Table 2-96 • ABPS Performance Specifications (SAR 25381).	2-82
	The test condition values for operating current (ICC33A, typical) were changed in Table 2-99 • Voltage Regulator (SAR 26465).	2-87
	Figure 2-45 • Typical Output Voltage was revised to add legends for the three curves, stating the load represented by each (SAR 25247).	2-88
	The "SmartFusion Programming" chapter was moved to this document from the SmartFusion Subsystem Microcontroller User's Guide (SAR 26542). The "Typical Programming and Erase Times" section was added to this chapter.	4-7
	Figure 4-1 • TRSTB Logic was revised to change 1.5 V to "VJTAG (1.5 V to 3.3 V nominal)" (SAR 24694).	4-8

Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

E-mail: sales.support@microsemi.com

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